

**ELECTRO-LUMINESCENCE DEVICE INCLUDING A THIN
FILM TRANSISTOR AND METHOD OF FABRICATING AN
ELECTRO-LUMINESCENCE DEVICE**

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ABSTRACT OF THE DISCLOSURE

An electro-luminescence device including an electro-luminescence element and a thin film transistor electrically connected to the electro-luminescence element. The thin film transistor includes a gate electrode formed over a substrate, an insulating layer formed over the gate electrode, and a first semiconductor pattern formed over the insulating layer. An etch stop layer is formed over the first semiconductor layer. A second semiconductor pattern is formed over the etch stop layer at one side of the etch stop layer, and a third semiconductor pattern is formed over the etch stop layer at another side of the etch stop layer. A source electrode is formed over the second semiconductor pattern, and a drain electrode is formed over the third semiconductor pattern.

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